# N-Channel 200-V (D-S) MOSFET

## **Key Features:**

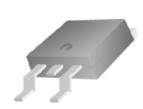
- Low r<sub>DS(on)</sub> trench technology
- · Low thermal impedance
- · Fast switching speed

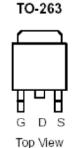
| Typical | l Applications: |
|---------|-----------------|
|---------|-----------------|

- White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

| PRODUCT SUMMARY     |                             |        |  |  |
|---------------------|-----------------------------|--------|--|--|
| V <sub>DS</sub> (V) | $r_{DS(on)}(m\Omega)$       | I□ (A) |  |  |
| 200                 | 240 @ V <sub>GS</sub> = 10V | 29     |  |  |







| ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED) |                      |                 |            |       |  |  |  |
|---|----------------------|-----------------|------------|-------|--|--|--|
| Parameter   |                      |                 | Limit      | Units |  |  |  |
| Drain-Source Voltage  |                      |                 | 200        | V     |  |  |  |
| Gate-Source Voltage   |                      |                 | ±20        | V     |  |  |  |
| Continuous Drain Current T <sub>C</sub> =25°C                           |                      | I <sub>D</sub>  | 29         | Α     |  |  |  |
| Pulsed Drain Current <sup>a</sup>                                       |                      | I <sub>DM</sub> | 100        | A     |  |  |  |
| Continuous Source Current (Diode Conduction) T <sub>C</sub> =25°C       |                      | I <sub>S</sub>  | 29         | Α     |  |  |  |
| Power Dissipation   | T <sub>C</sub> =25°C | $P_{D}$         | 300        | W     |  |  |  |
| Operating Junction and Storage Temperature Range                        |                      |                 | -55 to 150 | °C    |  |  |  |

| THERMAL RESISTANCE RATINGS               |                 |         |       |  |  |  |
|--|-----------------|---------|-------|--|--|--|
| Parameter                                | Symbol          | Maximum | Units |  |  |  |
| Maximum Junction-to-Ambient <sup>a</sup> | $R_{\theta JA}$ | 62.5    | °C/W  |  |  |  |
| Maximum Junction-to-Case                 | $R_{\theta JC}$ | 0.5     | C/VV  |  |  |  |

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### Notes

a. Pulse width limited by maximum junction temperature

### **Electrical Characteristics**

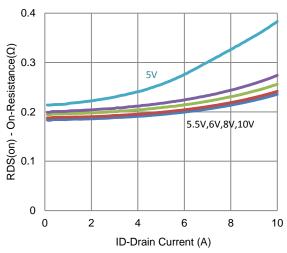
| Parameter                           | Symbol              | Test Conditions  | Min | Тур  | Max        | Unit |  |  |
|-------------------------------------|---------------------|--|-----|------|------------|------|--|--|
| Static                              |                     |  |     |      |            |      |  |  |
| Gate-Source Threshold Voltage       | $V_{GS(th)}$        | $V_{DS} = V_{GS}$ , $I_D = 250 \text{ uA}$                                 | 1   |      |            | V    |  |  |
| Gate-Body Leakage                   | I <sub>GSS</sub>    | $V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$                          |     |      | ±100       | nA   |  |  |
| Zero Gate Voltage Drain Current     | I <sub>DSS</sub>    | $V_{DS} = 160 \text{ V}, V_{GS} = 0 \text{ V}$                             |     |      | 1<br>25 uA |      |  |  |
| Zero Gate voltage Drain Current     | DSS                 | $V_{DS} = 160 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$ |     |      |            |      |  |  |
| On-State Drain Current <sup>a</sup> | I <sub>D(on)</sub>  | $V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$                              | 40  |      |            | Α    |  |  |
| Drain-Source On-Resistance a        | r <sub>DS(on)</sub> | $V_{GS} = 10 \text{ V}, I_{D} = 10 \text{ A}$                              |     |      | 240        | mΩ   |  |  |
| Forward Transconductance a          | $g_{fs}$            | $V_{DS} = 15 \text{ V}, I_{D} = 10 \text{ A}$                              |     | 32   |            | S    |  |  |
| Diode Forward Voltage <sup>a</sup>  | $V_{SD}$            | $I_{S} = 15 \text{ A}, V_{GS} = 0 \text{ V}$                               |     | 0.86 |            | V    |  |  |
|                                     |                     | Dynamic <sup>b</sup>   |     |      |            |      |  |  |
| Total Gate Charge                   | $Q_g$               | $V_{DS} = 100 \text{ V}, V_{GS} = 5.5 \text{ V},$                          |     | 13   |            |      |  |  |
| Gate-Source Charge                  | $Q_{gs}$            | $I_{D} = 5 \text{ A}$  |     | 6.2  |            | nC   |  |  |
| Gate-Drain Charge                   | $Q_gd$              | ig = 3 / (   |     | 6.6  |            |      |  |  |
| Turn-On Delay Time                  | t <sub>d(on)</sub>  | $V_{DS} = 100 \text{ V}, R_{L} = 20 \Omega,$                               |     | 14   |            |      |  |  |
| Rise Time                           | t <sub>r</sub>      | $I_{DS} = 100 \text{ V}, \text{ KL} = 20 \Omega,$ $I_{D} = 5 \text{ A},$   |     | 10   |            | ns   |  |  |
| Turn-Off Delay Time                 | t <sub>d(off)</sub> | $V_{GEN} = 10 \text{ V}, R_{GEN} = 6 \Omega$                               |     | 26   |            | 115  |  |  |
| Fall Time                           | t <sub>f</sub>      | VGEN - 10 V, NGEN 0 12   |     | 10   |            |      |  |  |
| Input Capacitance                   | C <sub>iss</sub>    |  |     | 1482 |            |      |  |  |
| Output Capacitance                  | C <sub>oss</sub>    | $V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ Mhz}$           |     | 110  |            | pF   |  |  |
| Reverse Transfer Capacitance        | $C_{rss}$           |  |     | 88   |            |      |  |  |

#### Notes

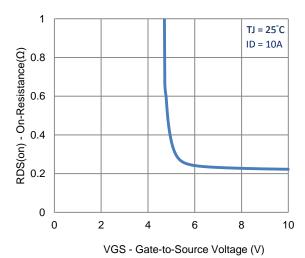
- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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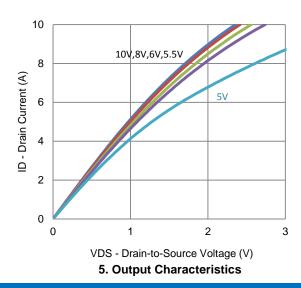
## **Typical Electrical Characteristics**

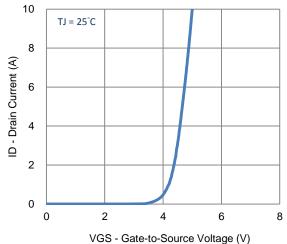


#### 1. On-Resistance vs. Drain Current

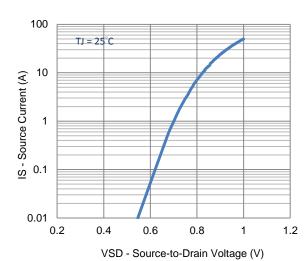


3. On-Resistance vs. Gate-to-Source Voltage

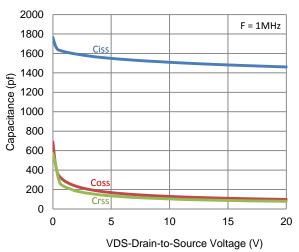




2. Transfer Characteristics

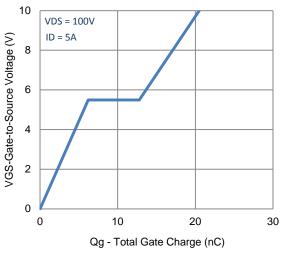


4. Drain-to-Source Forward Voltage

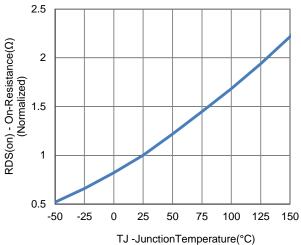


6. Capacitance

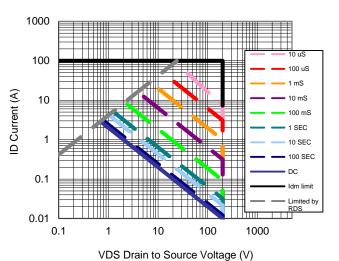
## **Typical Electrical Characteristics**



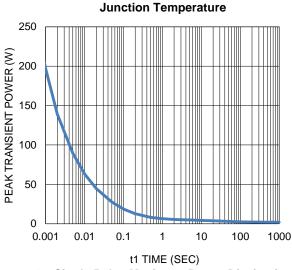
7. Gate Charge



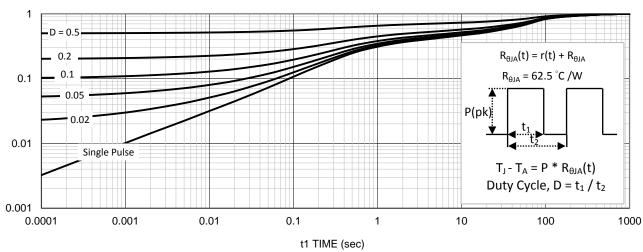
8. Normalized On-Resistance Vs



9. Safe Operating Area

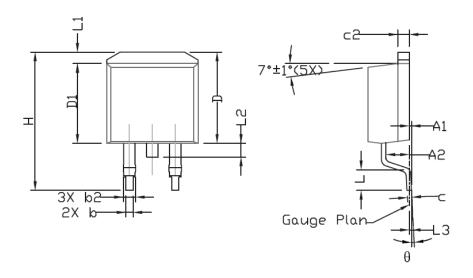


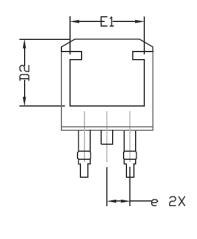
10. Single Pulse Maximum Power Dissipation



11. Normalized Thermal Transient Junction to Ambient

# **Package Information**





| CVMDEI | DIMENS. | IONAL F | REQMTS | INCHES REQMTS |         |       |
|--------|---------|---------|--------|---------------|---------|-------|
| SYMBOL | MIN     | NDM     | MAX    | MIN           | NDM     | MAX   |
| A      | 4,30    | 4.57    | 4,72   | 0.169         | 0.180   | 0.186 |
| A1     | 0       |         | 0,25   | 0             |         | 0.010 |
| A2     | 2,47    | 2.57    | 2,67   | 0.097         | 0.101   | 0.105 |
| b      | 0.69    | 0,813   | 0.94   | 0.027         | 0.032   | 0.037 |
| b2     | 1.17    | 1.27    | 1.45   | 0.046         | 0.050   | 0.057 |
| С      | 0.48    | 0,50    | 0.60   | 0.019         | 0.020   | 0.024 |
| c2     | 1.17    | 1.27    | 1.37   | 0.046         | 0,050   | 0,054 |
| D      | 9,80    | 10.05   | 10,30  | 0.386         | 0,396   | 0.406 |
| D1     | 8,64    | 8.78    | 9,65   | 0,340         | 0,346   | 0,380 |
| D2     | 7.12    | 7.37    | 7,62   | 0.280         | 0,290   | 0,300 |
| E      | 9,70    | 10.15   | 10.54  | 0.382         | 0,400   | 0.415 |
| E1     | 8,00    | 8,20    | 8,40   | 0.315         | 0,323   | 0.331 |
| е      | 2.      | 54 BSC  | ,      | 0.            | 100 BSC | ,     |
| H      | 14,99   | 15.24   | 15,49  | 0.590         | 0.600   | 0.610 |
| L      | 1,78    | 2.29    | 2.79   | 0.070         | 0.090   | 0.110 |
| L1     | 1.02    | 1.27    | 1.52   | 0.040         | 0.050   | 0,060 |
| L2     |         |         | 1.75   |               |         | 0.069 |
| L3     |         | 0,254   |        |               | 0.010   |       |
| θ      | 0°      |         | 8*     | 0°            |         | 8*    |